



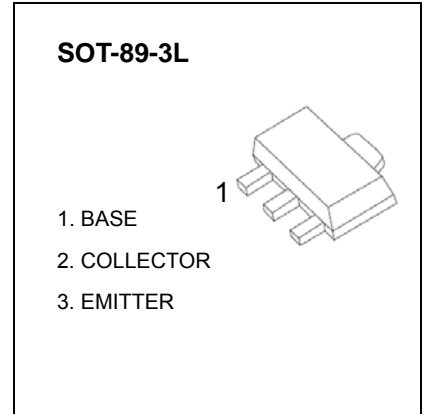
**SOT-89-3L Plastic-Encapsulate Transistors**

**CXT5551** TRANSISTOR (NPN)

**FEATURES**

- Switching and amplification in high voltage  
Applications such as telephony
- Low current(max. 600mA)
- High voltage(max.180V)

**Marking: 1G6**



**MAXIMUM RATINGS (T<sub>a</sub>=25°C unless otherwise noted)**

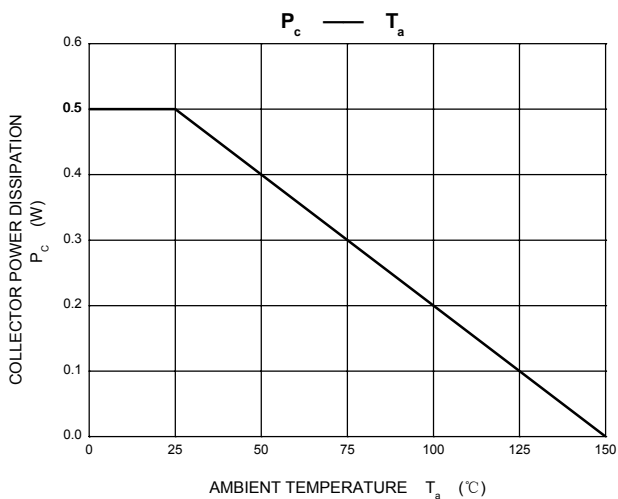
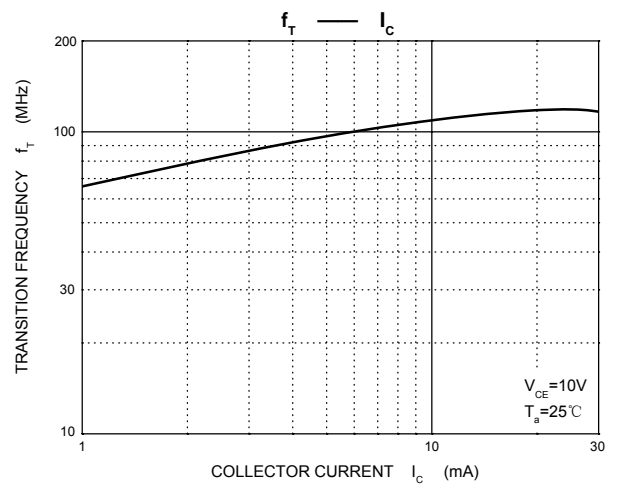
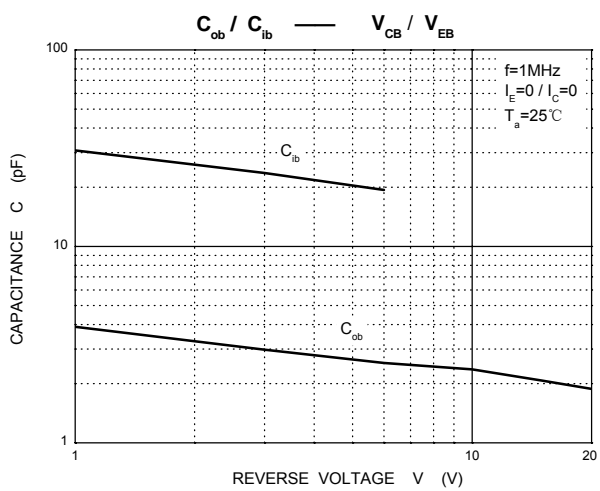
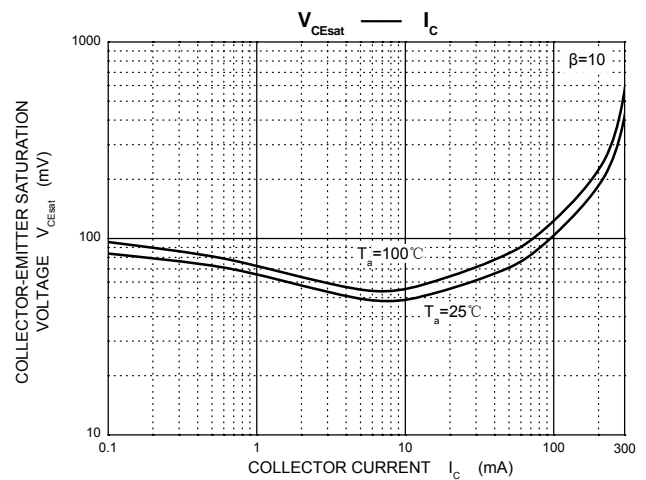
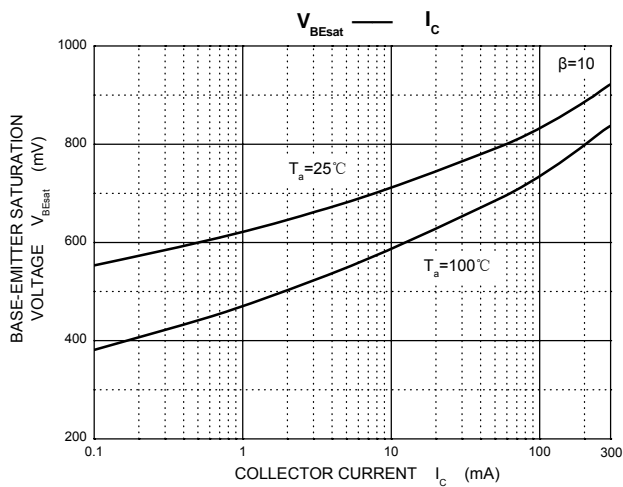
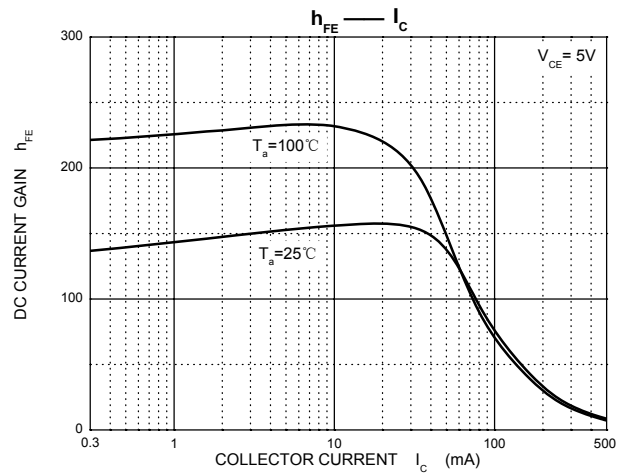
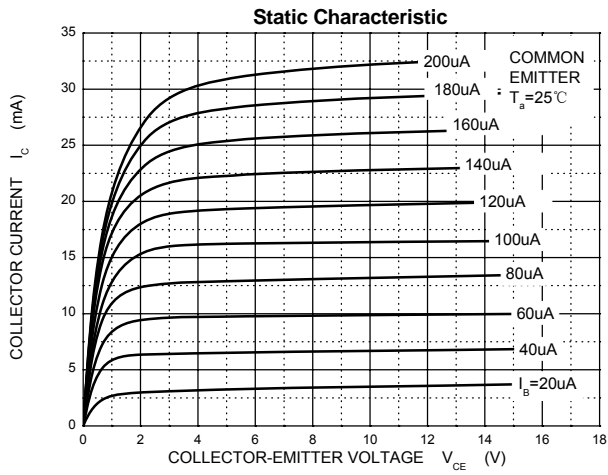
Symbol	Parameter	Value	Unit
V <sub>CB0</sub>	Collector-Base Voltage	180	V
V <sub>CEO</sub>	Collector-Emitter Voltage	160	V
V <sub>EBO</sub>	Emitter-Base Voltage	6	V
I <sub>C</sub>	Collector Current -Continuous	0.6	A
P <sub>C</sub>	Collector Power Dissipation	0.5	W
T <sub>J</sub>	Junction Temperature	150	°C
T <sub>stg</sub>	Storage Temperature	-65~150	°C

**ELECTRICAL CHARACTERISTICS (T<sub>a</sub>=25°C unless otherwise specified)**

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
<b>Collector-base breakdown voltage</b>	V <sub>(BR)CBO</sub>	I <sub>C</sub> =100μ A, I <sub>E</sub> =0	180			V
<b>Collector-emitter breakdown voltage</b>	V <sub>(BR)CEO</sub>	I <sub>C</sub> =1mA, I <sub>B</sub> =0	160			V
<b>Emitter-base breakdown voltage</b>	V <sub>(BR)EBO</sub>	I <sub>E</sub> =10 μ A, I <sub>C</sub> =0	6			V
<b>Collector cut-off current</b>	I <sub>CBO</sub>	V <sub>CB</sub> =120V, I <sub>E</sub> =0			50	nA
<b>Emitter cut-off current</b>	I <sub>EBO</sub>	V <sub>EB</sub> =4V, I <sub>C</sub> =0			50	nA
<b>DC current gain</b>	h <sub>FE(1)</sub>	V <sub>CE</sub> =5V, I <sub>C</sub> =1mA	80			
	h <sub>FE(2)</sub>	V <sub>CE</sub> =5V, I <sub>C</sub> =10mA	80		300	
	h <sub>FE(3)</sub>	V <sub>CE</sub> =5V, I <sub>C</sub> =50mA	30			
<b>Collector-emitter saturation voltage</b>	V <sub>CE(sat)</sub>	I <sub>C</sub> =10mA, I <sub>B</sub> =1mA			0.15	V
	V <sub>CE(sat)</sub>	I <sub>C</sub> =50mA, I <sub>B</sub> =5mA			0.2	V
<b>Base-emitter voltage</b>	V <sub>BE(sat)</sub>	I <sub>C</sub> =10mA, I <sub>B</sub> =1mA			1	V
	V <sub>BE(sat)</sub>	I <sub>C</sub> =50mA, I <sub>B</sub> =5mA			1	V
<b>Transition frequency</b>	f <sub>T</sub>	V <sub>CE</sub> =10V, I <sub>C</sub> =10mA, f=100MHZ	100			MHZ
<b>Collector output capacitance</b>	C <sub>ob</sub>	V <sub>CB</sub> =10V, I <sub>E</sub> =0, f=1MHZ			6	pF
<b>Noise figure</b>	NF	V <sub>CE</sub> =5V, I <sub>C</sub> =0.2mA, f=10Hzto15.7KHZ, R <sub>s</sub> =10Ω			8	dB

# Typical Characteristics

# CXT5551



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